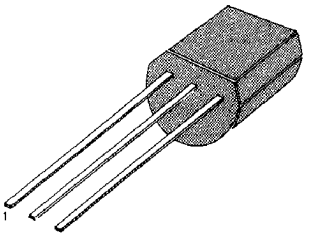
SS8550 PNP EPITAXIAL SILICON TRANSISTOR

2W OUTPUT AMPLIFIER OF PORTABLE RADIOS IN CLASS B PUSH-PULL OPERATION.

- Complimentary to SS8050
- Collector Current: I_C= -1.5A
- Collector Dissipation: P_C=2W (T_C=25°C)

TO-92



1. Emitter 2. Base 3. Collector

ABSOLUTE MAXIMUM RATINGS (T_A=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-1.5	A
Collector Dissipation	P_C	1	W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-65 ~ 150	°C

ELECTRICAL CHARACTERISTICS (T_A=25°C)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C= -100μA, I_E=0	-40			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C= -2mA, I_B=0	-25			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E= -100μA, I_C=0	-6			V
Collector Cut-off Current	I_{CBO}	V_{CB}= -35V, I_E=0			-100	nA
Emitter Cut-off Current	I_{EBO}	V_{EB}= -6V, I_C=0			-100	nA
DC Current Gain	h_{FE1}	V_{CE}= -1V, I_C= -5mA	45	170		
	h_{FE2}	V_{CE}= -1V, I_C= -100mA	85	160	300	
	h_{FE3}	V_{CE}= -1V, I_C= -800mA	40	80		
Collector-Emitter Saturation Voltage	V_{CE} (sat)	I_C= -800mA, I_B= -80mA		-0.28	-0.5	V
Base-Emitter Saturation Voltage	V_{BE} (sat)	I_C= -800mA, I_B= -80mA		-0.98	-1.2	V
Base-Emitter Voltage	V_{BE}	V_{CE}= -1V, I_C= -10mA		-0.66	-1.0	V
Output Capacitance	C_{OB}	V_{CB}= -10V, I_E=0 f=1MHz		15		pF
Current Gain-Bandwidth Product	f_T	V_{CE}= -10V, I_C= -50mA	100	200		MHz

h_{FE}(2) CLASSIFICATION

Classification	B	C	D
h_{FE}(2)	85-160	120-200	160-300

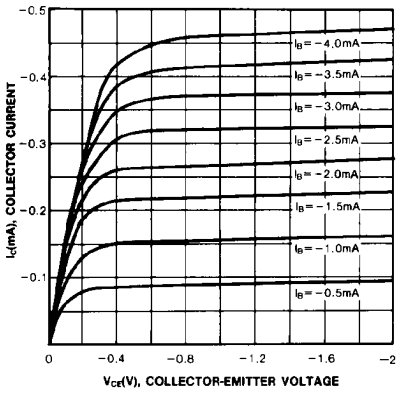
Rev. B

FAIRCHILD SEMICONDUCTOR™

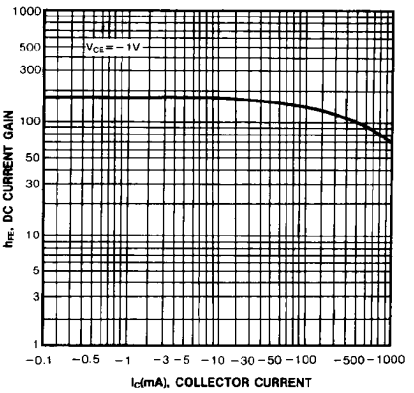
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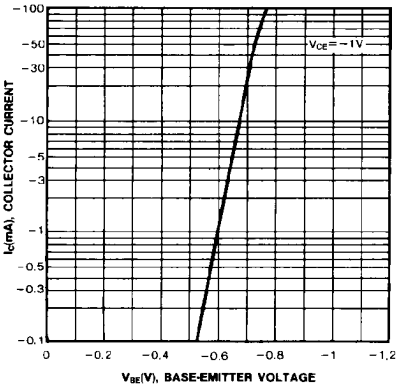
STATIC CHARACTERISTIC



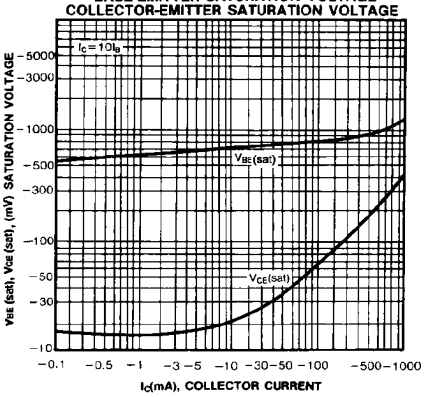
DC CURRENT GAIN



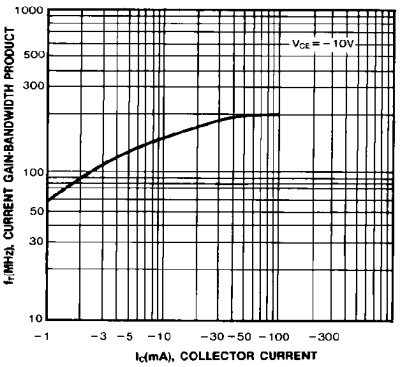
BASE-EMITTER ON VOLTAGE



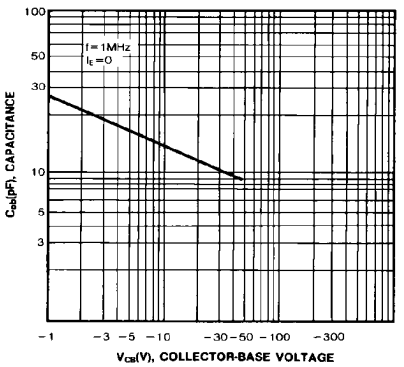
BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



CURRENT GAIN-BANDWIDTH PRODUCT



COLLECTOR OUTPUT CAPACITANCE



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